



STB80NF10 STP80NF10

N-channel 100V - 0.012Ω - 80A - TO-220 / D²PAK
Low gate charge STripFET™ II Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D ⁽¹⁾
STP80NF10	100V	<0.015Ω	80A
STB80NF10	100V	<0.015Ω	80A

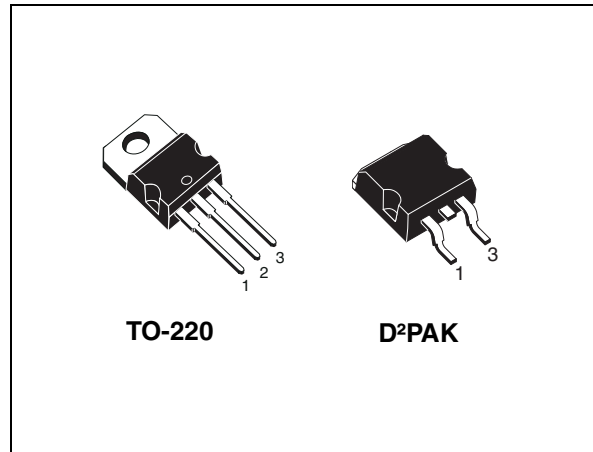
- Exceptional dv/dt capability
- 100% Avalanche tested
- Application oriented characterization

Description

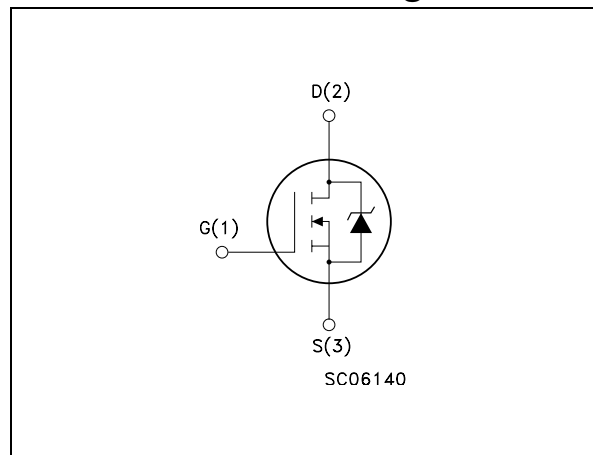
This Power MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency isolated DC-DC converters for Telecom and Computer application. It is also intended for any application with low gate charge drive requirements.

Applications

- Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STP80NF10	P80NF10@	TO-220	Tube
STB80NF10T4	B80NF10@	D ² PAK	Tape & reel

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	100	V
V_{GS}	Gate- source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	80	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	80	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	300	W
	Derating factor	2	W/ $^\circ\text{C}$
$dv/dt^{(3)}$	Peak diode recovery voltage slope	7	V/ns
$E_{AS}^{(4)}$	Single pulse avalanche energy	350	mJ
T_{stg} T_j	Storage temperature Operating junction temperature	-55 to 175	$^\circ\text{C}$

1. Limited by package
2. Pulse width limited by safe operating area
3. $I_{SD} < 80\text{A}$, $di/dt < 300\text{A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$
4. Starting $T_j = 25^\circ\text{C}$, $I_D = 80\text{A}$, $V_{DD} = 50\text{V}$

Table 2. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case Max	0.5	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient Max	62.5	$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 250\mu\text{A}$, $V_{GS} = 0$	100			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating @ } 125^{\circ}\text{C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{V}$, $I_D = 40\text{A}$		0.012	0.015	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 25\text{V}$, $I_D = 40\text{A}$		50		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$		5500 700 175		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 50\text{V}$, $I_D = 80\text{A}$, $V_{GS} = 10\text{V}$		135 23 51.3	182	nC nC nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5 %

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50V$, $I_D = 40A$, $R_G = 4.7\Omega$, $V_{GS} = 10V$ (see Figure 14)		26		ns
t_r	Rise time			80		ns
$t_{d(off)}$	Turn-off-delay time			116		ns
t_f	Fall time			60		ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 80A$, $V_{GS} = 0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 80A$, $V_{DD} = 50V$ $di/dt = 100A/\mu s$, $T_J = 150^\circ C$		106		ns
Q_{rr}	Reverse recovery charge			450		nC
I_{RRM}	Reverse recovery current			8.5		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration=300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

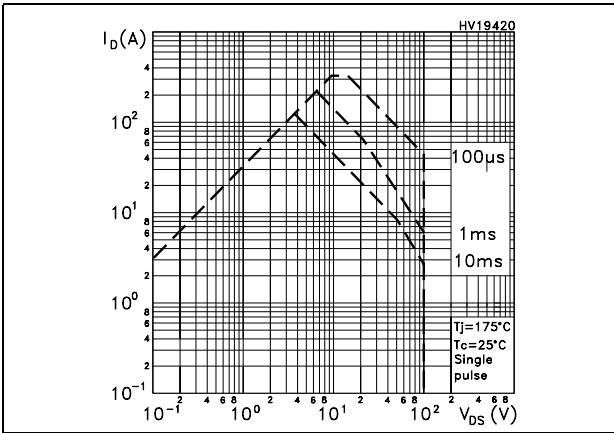


Figure 2. Thermal impedance

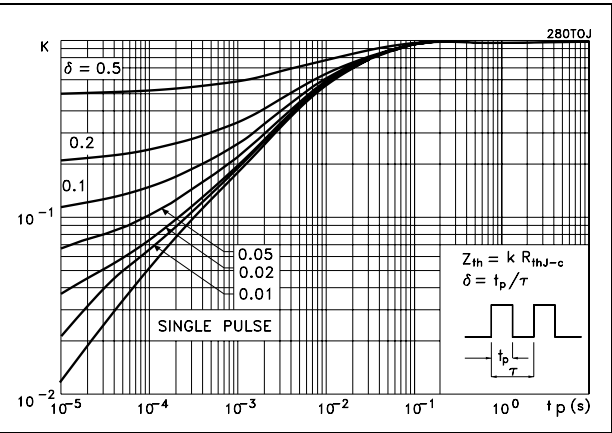


Figure 3. Output characteristics

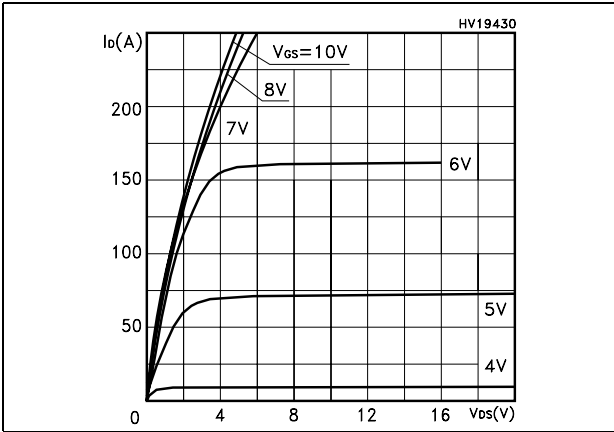


Figure 4. Transfer characteristics

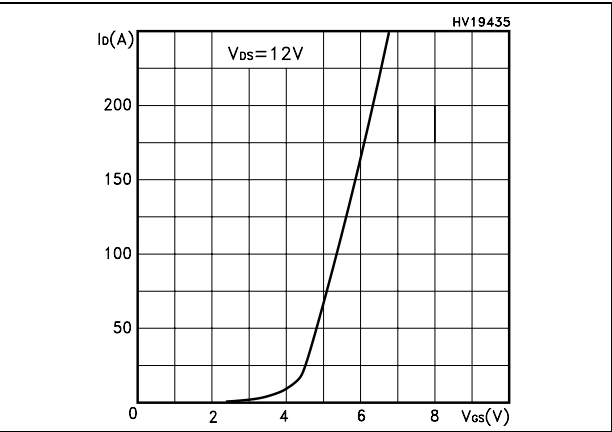


Figure 5. Transconductance

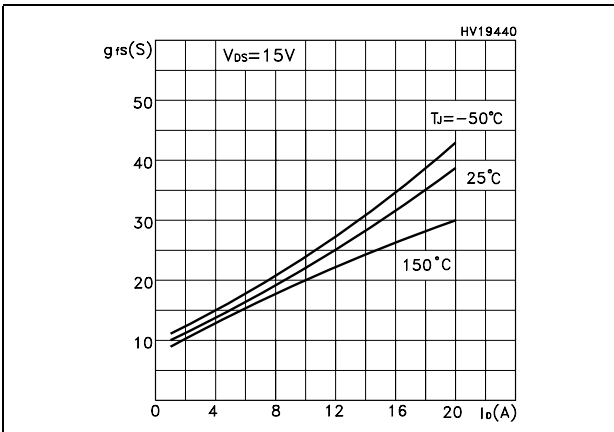


Figure 6. Static drain-source on resistance

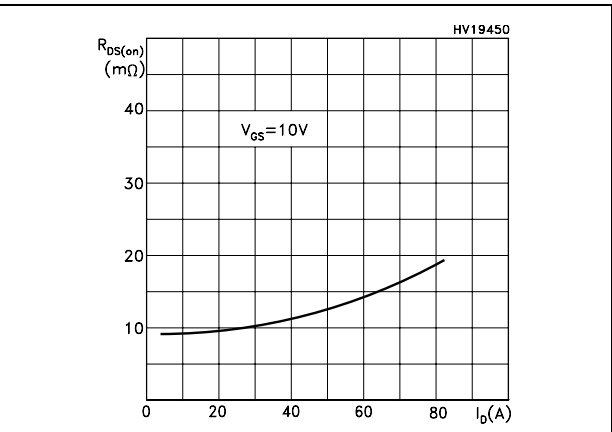


Figure 7. Gate charge vs gate-source voltage Figure 8. Capacitance variations

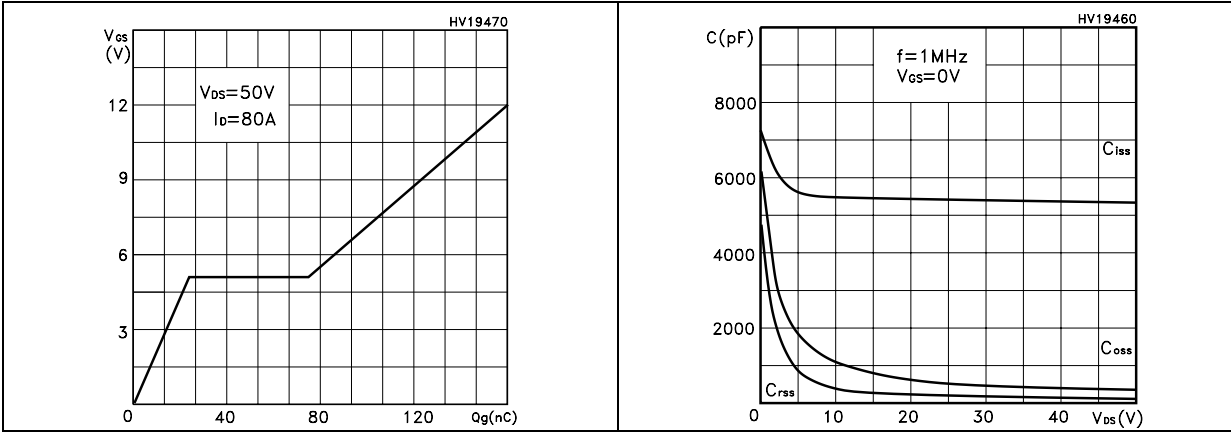


Figure 9. Normalized gate threshold voltage vs temperature Figure 10. Normalized on resistance vs temperature

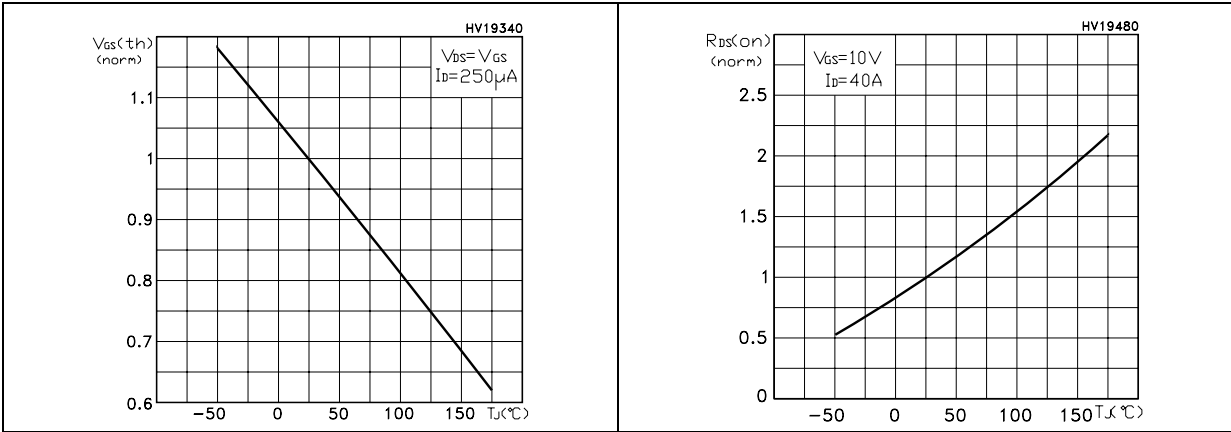
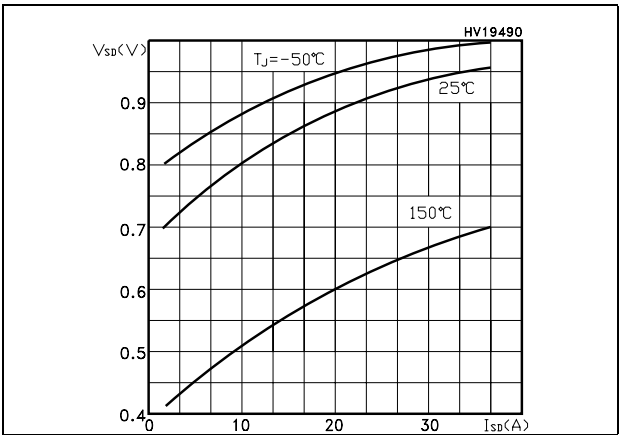


Figure 11. Source-drain diode forward characteristics



3 Test circuit

Figure 12. Switching times test circuit for resistive load

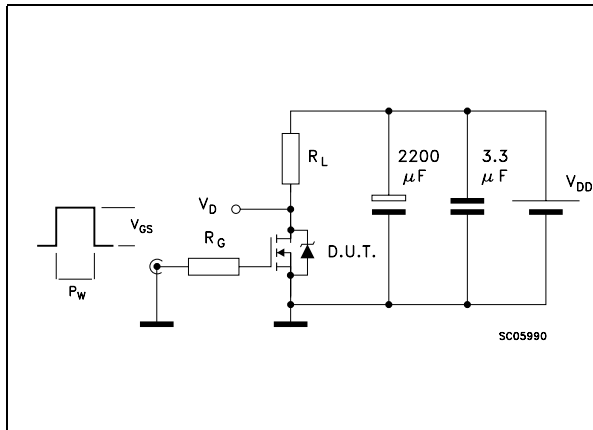


Figure 13. Gate charge test circuit

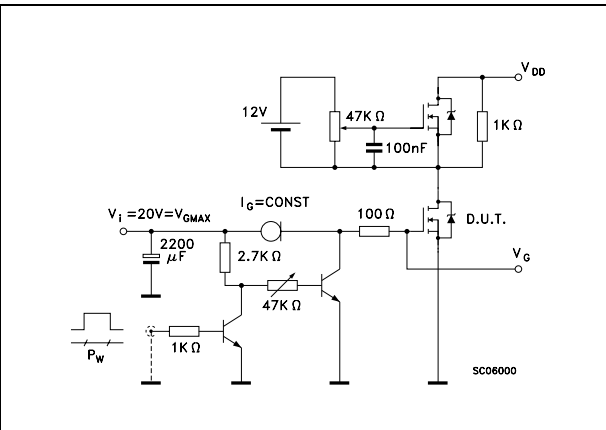


Figure 14. Test circuit for inductive load switching and diode recovery times

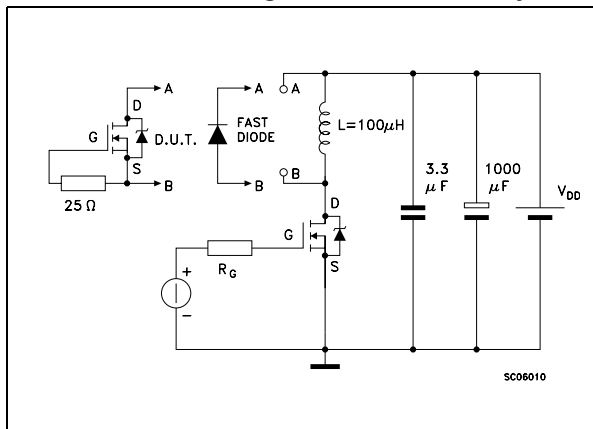


Figure 15. Unclamped inductive load test circuit

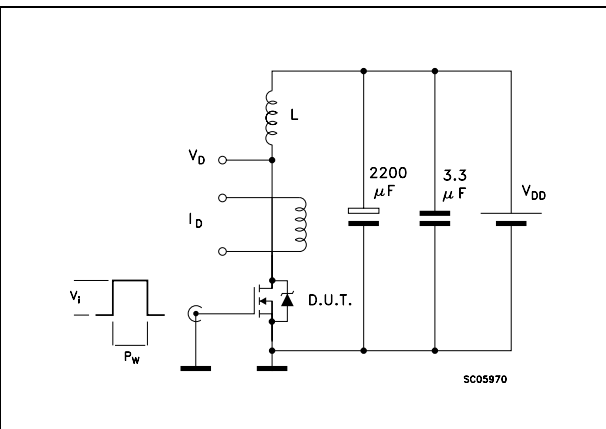


Figure 16. Unclamped inductive waveform

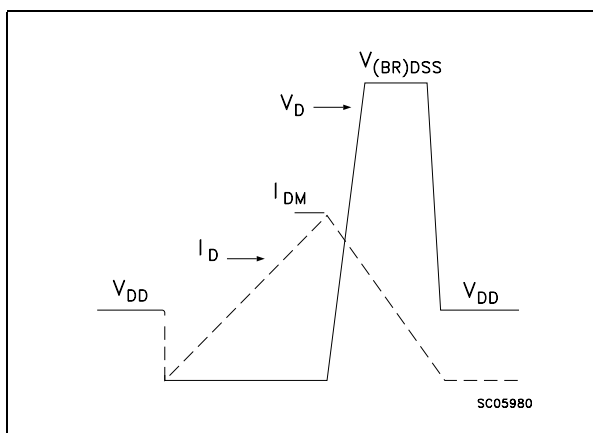
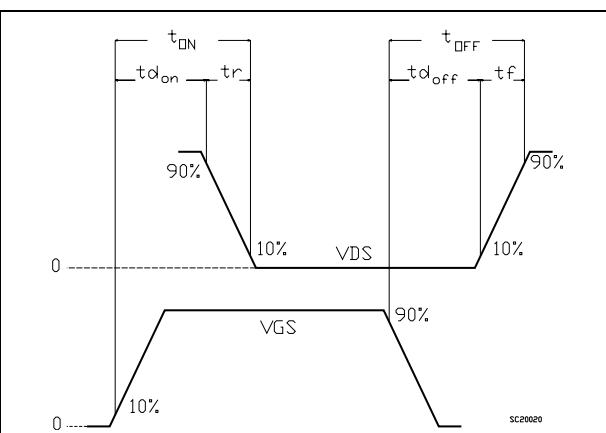


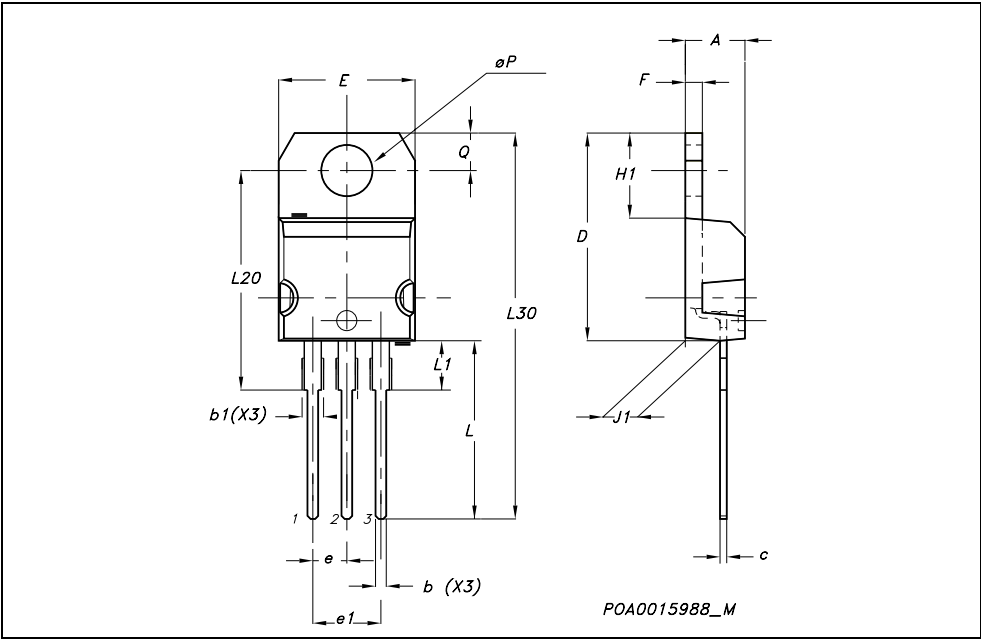
Figure 17. Switching time waveform



4 Package mechanical data

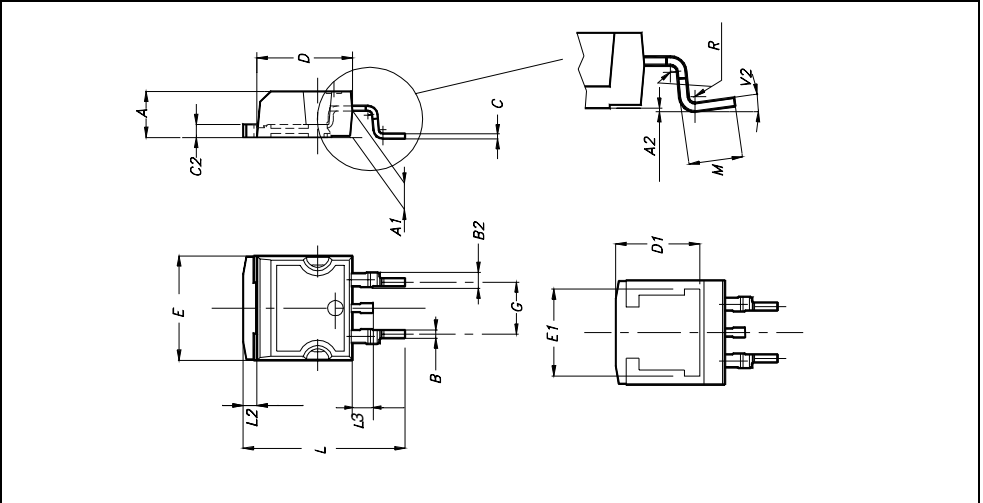
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-220 MECHANICAL DATA						
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



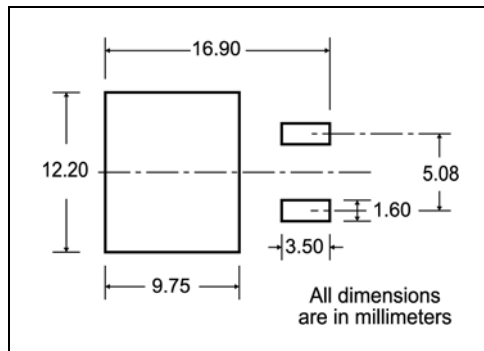
D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			

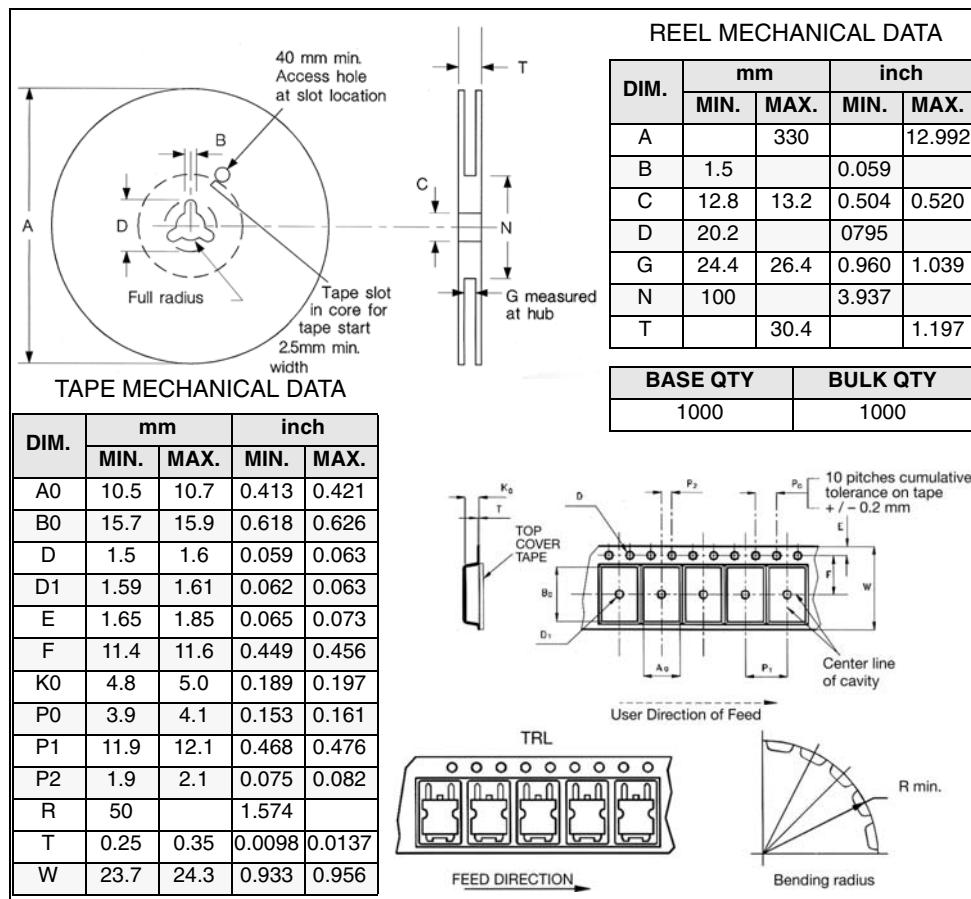


5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT



* on sales type

6 Revision history

Table 7. Revision history

Date	Revision	Changes
04-Nov-2003	8	New datasheet according to PCN DSG-TRA/03/382
13-Dec-2004	9	D ² PAK inserted
16-Dec-2004	10	@ inserted in table 2 for TO-220 marking
27-Jan-2005	11	New value in table 3
22-Feb-2005	12	Id value changed
28-Feb-2005	13	New value in table 3
01-Mar-2005	14	Vgs value changed
06-Apr-2006	15	The document has been reformatted
25-Jan-2007	16	Typo mistake on page 1 (order codes)

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